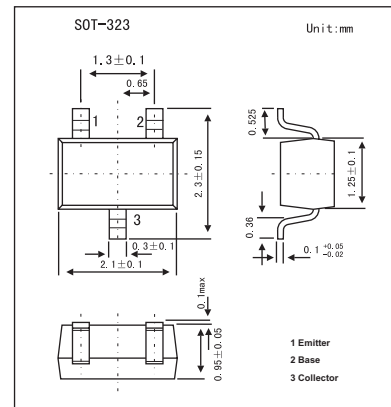


Silicon NPN Epitaxial

2SC4253

■ Features

- Good linearity of fr.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	30	V
Collector-emitter voltage	V_{CEO}	25	V
Emitter-base voltage	V_{EBO}	4	V
Collector current	I_C	50	mA
Base current	I_B	25	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 30\text{ V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 3\text{ V}, I_C = 0$			0.1	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1\text{ mA}, I_B = 0$	25			V
DC current gain	h_{FE}	$V_{CE} = 10\text{ V}, I_C = 10\text{ mA}$	20	70	200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 15\text{ mA}, I_B = 1.5\text{ mA}$			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 15\text{ mA}, I_B = 1.5\text{ mA}$			1.5	V
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$		1.1	1.6	pF
Collector-base time constant	$C_{c,rb}'$	$V_{CB} = 10\text{ V}, I_C = 1\text{ mA}, f = 30\text{ MHz}$			25	ps
Transition frequency	f_T	$V_{CE} = 10\text{ V}, I_C = 10\text{ mA}$	250	600		MHz

■ Marking

Marking	HH